

Small Signal Switching Diodes

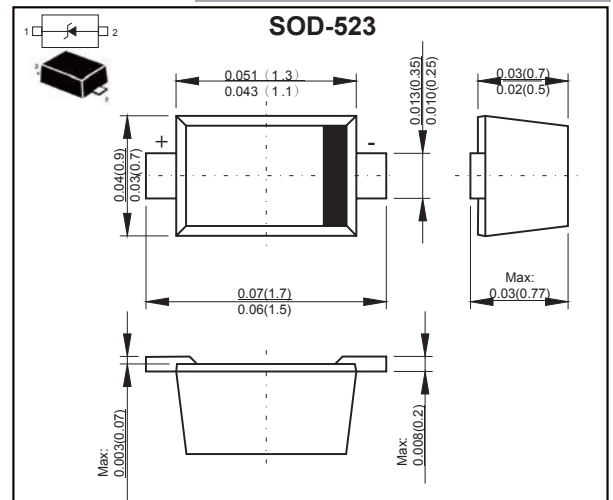
VOLTAGE RANGE: 100V
PEAK PULSE POWER: 150mW

FEATURES

- Fast switching devices
- Low Reverse Current
- Matte Tin (Sn) Lead finish
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

MECHANICAL DATA

- Case: SOD-523 Micro SMD package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

Symbol	Parameter	Value	Unit
V_{RM}	Non-Repetitive Peak Reverse Voltage	100	V
V_R	Reverse Voltage	75	V
V_{RRM}	Peak Repetitive Reverse Voltage		
V_{RWM}	Working Peak Reverse Voltage		
$V_{R(RMS)}$	RMS Reverse Voltage	53	V
I_O	Average Rectified Output Current	150	mA
I_{FM}	Forward Continuous Current	300	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current@t= 8.3ms	2	A
P_D	Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

Electrical Specification ($T_A=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=1\mu A$	75			V
Reverse current	I_R	$V_R=75V$			1	μA
		$V_R=20V$			25	nA
Forward voltage	V_F	$I_F=1mA$			0.715	V
		$I_F=10mA$			0.855	V
		$I_F=50mA$			1	V
		$I_F=150mA$			1.25	V
Total capacitance	C_{tot}	$V_R=0V, f=1MHz$			2	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1*I_R, R_L=100\Omega$			4	ns

MARKING: T4

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

